

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Yi Ding
Assignee: Mosel Vitelic, Inc.
Title: Nonvolatile Memory Cell With Multiple Floating Gates Formed After The Select Gate And Having Upward Protrusions
Application No.: Unassigned Filing Date: Filed Herewith
Examiner: Unassigned Group Art Unit: Unassigned
Docket No.: M-15241 US

San Jose, California
July 30, 2003

Mail Stop Patent Application
Commissioner For Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR § 1.97(b)

Dear Sir:

Pursuant to 37 CFR § 1.56, § 1.97 and § 1.98, the documents listed on the accompanying form PTO-1449 are called to the attention of the Examiner for the above patent application. Copies of these documents are enclosed.

Citation of these documents shall not be construed as:

1. an admission that the documents are necessarily prior art with respect to the instant invention;
2. a representation that a search has been made, other than as described above; or
3. an admission that the information cited herein is, or is considered to be material to patentability as defined in § 1.56(b).

No fee is believed to be required. If a fee is required for this Information Disclosure Statement, please charge the fee to Deposit Account No. 50-2257. This paper is being submitted in duplicate.

EXPRESS MAIL LABEL NO.:

EE 508 123 313 US

Respectfully submitted,

Michael Shenker

Michael Shenker
Attorney for Applicant(s)
Reg. No. 34,250

U.S. Department of Commerce, Patent and Trademark Office		Atty Docket No.	Serial No.
		M-15241 US	Unassigned
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Applicant(s)	
		Yi Ding	
		Filing Date	Group
		Filed Herewith	Unassigned

U.S. Patent Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	5,402,371	28 Mar. 1995	Ono			
	AB	5,856,943	5 Jan. 1999	Jenq			
	AC	6,057,575	2 May 2000	Jenq			
	AD	6,130,129	10 Oct. 2000	Chen			
	AE	6,134,144	17 Oct. 2000	Lin et al.			
	AF	6,171,909	9 Jan. 2001	Ding et al.			
	AG	6,200,856	13 Mar. 2001	Chen			
	AH	6,261,903	17 Jul. 2001	Chang et al.			
	AI	6,326,661	4 Dec. 2001	Dormans et al.			
	AJ	6,355,524	12 Mar. 2002	Tuan et al.			
	AK	6,365,457	2 Apr. 2002	Choi			

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	AL	Shirota, Riichiro "A Review of 256Mbit NAND Flash Memories and NAND Flash Future Trend," February 2000, Nonvolatile Memory Workshop in Monterey, California, pages 22-31.
	AM	Naruke, K.; Yamada, S.; Obi, E.; Taguchi, S.; and Wada, M. "A New Flash-Erase EEPROM Cell with A Sidewall Select-Gate On Its Source Side," 1989 IEEE, pages 604-606.
	AN	Wu, A.T.; Chan T.Y.; Ko, P.K.; and Hu, C. "A Novel High-Speed, 5-Volt Programming EPROM Structure With Source-Side Injection," 1986 IEEE, 584-587.
	AO	Mizutani, Yoshihisa; and Makita, Koji "A New EPROM Cell With A Sidewall Floating Gate Fro High-Density and High Performance Device," 1985 IEEE, 635-638.
	AP	Ma, Y.; Pang, C.S.; Pathak, J.; Tsao, S.C.; Chang, C.F.; Yamauchi, Y.; Yoshimi, M. "A Novel High Density Contactless Flash Memory Array Using Split-Gate Source-Side-Injection Cell for 5V-Only Applications," 1994 Symposium on VLSI Technology Digest of Technical Papers, pages 49-50.
	AQ	Mih, Rebecca et al. "0.18um Modular Triple Self-Aligned Embedded Split-Gate Flash Memory," 2000 Symposium on VLSI Technology Digest of Technical Papers, pages 120-121.
	AR	Ma, Yale et al., "A Dual-Bit Split-Gate EEPROM (DSG) Cell in Contactless Array for Single Vcc High Density Flash Memories," 1994 IEEE, 3.5.1-3.5.4.

Examiner	Date Considered
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.	

U.S. Department of Commerce, Patent and Trademark Office		Atty Docket No.	Serial No.
		M-15241 US	Unassigned
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		Applicant(s)	
(Use several sheets if necessary)		Yi Ding	
		Filing Date	Group
		Filed Herewith	Unassigned

U.S. Patent Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AS	6,437,360	20 Aug. 2002	Cho et al.			
	AT	6,438,036	20 Aug. 2002	Seki et al.			
	AU	6,486,023	26 Nov. 2002	Nagata			
	AV	6,541,324	1 Apr. 2003	Wang			
	AW	2002/0064071 A1	30 May 2002	Takahashi et al.			
	AX	2002/0197888 A1	26 Dec. 2002	Huang et al.			
	AY	6,266,278	24 Jul. 2001	Harari et al.			
	AZ	5,901,084	4 May 1999	Ohnakado			
	BA	6,518,618	11 Feb. 2003	Fazio et al.			
	BB	6,541,829	1 Apr. 2003	Nishinohara et al.			
	BC	6,414,872	2 Jul. 2002	Bergemont et al.			

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

	BD	Spinelli, Alessandro S., "Quantum-Mechanical 2D Simulation of Surface-and Buried-Channel p-MOS," 2000 International Conference on Simulation of Semiconductor Processes and Devices: SISPAD 2000, Seattle, WA September 6-8, 2000
	BE	Kim, K.S. et al. "A Novel Dual String NOR (DuSnor) Memory Cell Technology Scalabe to the 256 Mbit and 1 Gbit Flash Memories," 1995 IEEE 11.1.1-11.1.4
	BF	Bergemont, A. et al. "NOR Virtual Ground (NVG)- A New Scaling Concept for Very High Density FLAS EEPROM and its Implementation in a 0.5 um Process," 1993 IEEE 2.2.1-2.2.4
	BG	Van Duuren, Michiel et al., "Compact poly-CMP Embedded Flash Memory Cells For One or Two Bit Storage," Philips Research Leuven, Kapeldreef 75, B3001 Leuven, Belgium, pages 73-74.
	BH	
	BI	
	BJ	

Examiner	Date Considered
----------	-----------------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.